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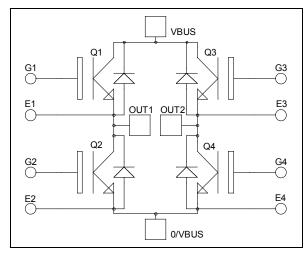


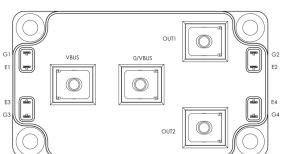




Full bridge High speed Trench + Field Stop IGBT4 Power Module

 $V_{CES} = 650V$ $I_{C} = 200A @ Tc = 60°C$





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- Very low stray inductance
- Kelvin emitter for easy drive

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

All ratings @ $T_i = 25$ °C unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		650	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	270	
I_{C}	$T_{\rm C}$ =	$T_C = 60$ °C	200	Α
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	540	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Power Dissipation		680	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$, $V_{CE} =$			75	μΑ	
**	Called a Facility of Called William	$V_{GE} = 15V$	$T_i = 25^{\circ}C$	1.4	1.85	2.3	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_{\rm C} = 200 A$	$T_{j} = 150^{\circ}C$		2.2		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3.2 \text{ mA}$		4.2	5.1	5.6	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				300	nA

Dynamic Characteristics (per IGBT)

·	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			12.2		
C_{oes}	Output Capacitance	$V_{CE} = 25V$	$V_{CE} = 25V$		0.43		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			0.36		
Q_{G}	Gate charge	$V_{GE} = 15V, I_{C} = V_{CE} = 480V$	200A		1260		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	hing (25°C)		19		ns
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			33		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400V$ $I_{C} = 200A$			197		
$T_{\rm f}$	Fall Time	$R_G = 1.8\Omega$		21			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 400V$ $I_{C} = 200A$ $R_{G} = 1.8\Omega$			19		ns
$T_{\rm r}$	Rise Time				29		
$T_{d(off)}$	Turn-off Delay Time				227		
T_{f}	Fall Time				22		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$	$T_j = 150$ °C		4.8		mJ
E_{off}	Turn off Energy	$I_C = 200A$ $R_G = 1.8\Omega$	$T_j = 150$ °C		4		1113
R_G	Integrated gate resistor				1		Ω
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bus} = 400V$ $t_p \le 5\mu s ; T_i = 150^{\circ}C$			1400		A
R_{thJC}	Junction to Case Thermal Resistance					0.22	°C/W

Diode ratings and characteristics (per diode)

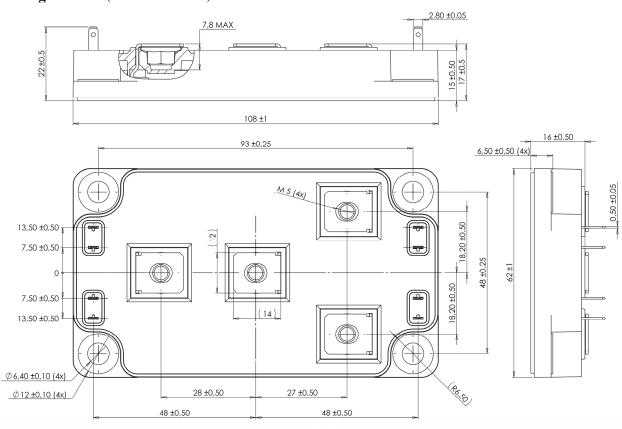
Symbol	naracteristic Test Conditions			Min	Тур	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					650	V
I_{RM}	Reverse Leakage Current	$V_R = 650V$				50	μΑ
I_F	DC Forward Current		$Tc = 25^{\circ}C$		200		A
V_{F}	Diode Forward Voltage	$I_F = 200A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
V F			$T_{i} = 150^{\circ}C$		1.5		V
f	Reverse Recovery Time	$I_F = 200A$ $V_P = 300V$ T_j	$T_j = 25^{\circ}C$		125		ns μC
t_{rr}			$T_{\rm j} = 150^{\circ}{\rm C}$		220		
0	Reverse Recovery Charge		$T_j = 25$ °C		9.4		
Q_{rr}			$T_{\rm j} = 150^{\circ}{\rm C}$		20		μC
E_{rr}	Reverse Recovery Energy	$T_{j} = 2$	$T_j = 25$ °C		2.2		mJ
Ľm			$T_{\rm j} = 150^{\circ}{\rm C}$		4.8		1113
R_{thJC}	Junction to Case Thermal Resistance					0.39	°C/W



Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_{J}	Operating junction temperature range			-40	175	
T_{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T_{STG}	Storage Temperature Range				125	
T_{C}	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Torque		For terminals	M5	2	3.5	
Wt	Package Weight				300	g

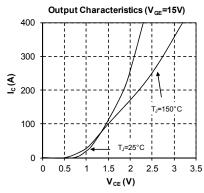
Package outline (dimensions in mm)

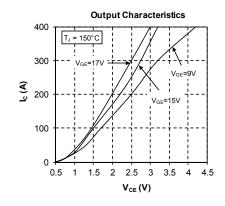


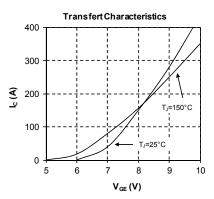
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

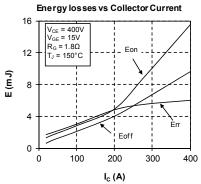


Typical Performance Curve

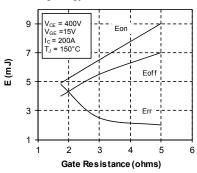












0.24

0.2

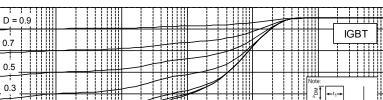
0.16

0.12

0.08 0.04

0.00001

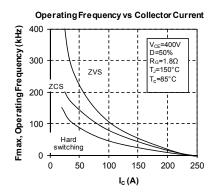
Thermallm pedance (°C/W)

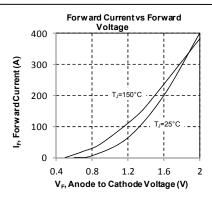


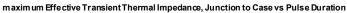
 $m\,axim\,um\,Effective\,Transient\,Thermal\,Impedance, Junction\,to\,Case\,vs\,\,Puls\,e\,Duration$

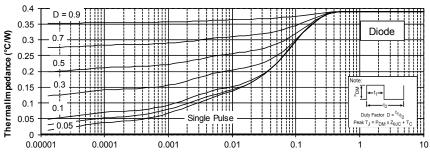


Power Matters.™









Rectangular Pulse Duration in Seconds



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